

## SNx4HCT125 Quadruple Bus Buffer Gates With 3-State Outputs

### 1 Features

- Operating voltage range of 4.5 V to 5.5 V
- High-current can drive up to 15 LSTTL loads
- Low power consumption, 80- $\mu$ A max  $I_{CC}$
- Typical  $t_{pd} = 12$  ns
- $\pm 6$ -mA output drive at 5 V
- Low input current of 1  $\mu$ A max
- Inputs are TTL-voltage compatible
- High-current 3-state outputs drive bus lines or buffer memory address registers

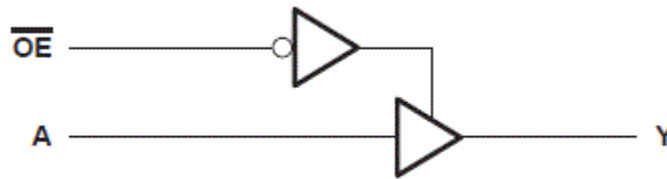
### 2 Description

The SNx4HCT125 contains four independent buffers with TTL-compatible inputs and 3-state outputs. Each gate performs the Boolean function  $Y = A$  in positive logic.

#### Device Information

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)
SN74HCT125D	SOIC (14)	8.65 mm $\times$ 3.90 mm
SN74HCT125N	PDIP (14)	19.31 mm $\times$ 6.35 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Functional Block Diagram



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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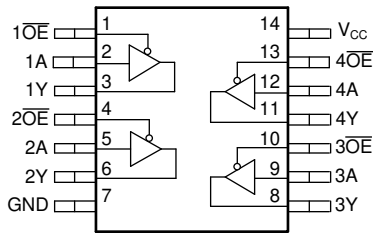
### 3 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

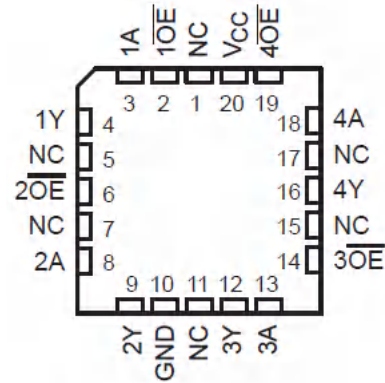
<b>Changes from Revision F (February 2022) to Revision G (October 2022)</b>	<b>Page</b>
• Increased R $\theta$ JA for packages: D (86 to 138.7); N (80 to 75.3).....	4

<b>Changes from Revision E (August 2003) to Revision F (February 2022)</b>	<b>Page</b>
• Updated the numbering, formatting, tables, figures, and cross-references throughout the document to reflect modern data sheet standards.....	1

### 4 Pin Configuration and Functions



**D, N, J or W Package  
14-Pin SOIC or PDIP  
Top View**



NC – No internal connection

**FK Package  
20-Pin LCCC  
Top View**

## 5 Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range	-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	(V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>CC</sub> )		±20 mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	(V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )		±20 mA
I <sub>O</sub>	Continuous output current	(V <sub>O</sub> = 0 to V <sub>CC</sub> )		±35 mA
V <sub>CC</sub> or GND	Continuous current through			±70 mA
T <sub>J</sub>	Junction temperature			150 °C
T <sub>stg</sub>	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 5.2 Recommended Operating Conditions<sup>(1)</sup>

		SN54HCT125 <sup>(2)</sup>			SN74HCT125			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V <sub>CC</sub>	Supply voltage	4.5	5	5.5	4.5	5	5.5	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V		2	2		V	
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V		0.8		0.8	V	
V <sub>I</sub>	Input voltage	0	V <sub>CC</sub>		0	V <sub>CC</sub>		V
V <sub>O</sub>	Output voltage	0	V <sub>CC</sub>		0	V <sub>CC</sub>		V
t <sub>t</sub>	Input transition rise/fall time	500		500		500	ns	
T <sub>A</sub>	Operating free-air temperature	-55	125		-40	85		°C

- (1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report Implications of Slow or Floating SMOS Inputs, literature number SCBA004.
- (2) SN54HCT125 is in product preview.

### 5.3 Thermal Information

THERMAL METRIC		D (SOIC)	N (PDIP)	UNIT
		14 PINS	14 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance <sup>(1)</sup>	138.7	75.3	°C/W
R <sub>θJC</sub>	Junction-to-case (top) thermal resistance	93.8	68.6	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	94.7	55.1	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	49.1	41.1	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	94.3	54.9	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

## 5.4 Electrical Characteristics

PARAMETER		TEST CONDITIONS <sup>(1)</sup>	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			SN54HCT125 <sup>(3)</sup>		SN74HCT125		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -20 μA	4.5	4.4	4.499		4.4		4.4	V	
		I <sub>OH</sub> = -6 mA		3.98	4.3		3.7		3.84		
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 20 μA	5.5		0.001	0.1		0.1	0.1	V	
		I <sub>OL</sub> = 6 mA			0.17	0.26		0.4	0.33		
I <sub>I</sub>	Input hold current	V <sub>I</sub> = V <sub>CC</sub> or 0	5.5		±0.1	±100		±1000	±1000	nA	
I <sub>OZ</sub>	Off-state output current	V <sub>o</sub> = V <sub>CC</sub> or 0	5.5		±0.01	±0.5		±10	±5	μA	
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> or 0. I <sub>O</sub> = 0	5.5			8		160	80	μA	
ΔI <sub>CC</sub> <sup>(2)</sup>	Supply-current change	One input at 0.5 V or 2.4 V, Other inputs at 0 or V <sub>CC</sub>	5.5		1.4	2.4		3	2.9	mA	
C <sub>i</sub>	Input capacitance		4.5 to 5.5		3	10		10 <sup>(4)</sup>	10	pF	

(1) V<sub>I</sub> = V<sub>IH</sub> or V<sub>IL</sub>, unless otherwise noted.

(2) This is the increase in supply current for each input that is at one of the specified TTL voltage levels, rather than 0 V or V<sub>CC</sub>.

(3) SN54HCT125 is in product preview.

(4) On products compliant to MIL-PRF-38535, this parameter is not production tested.

## 5.5 Switching Characteristics

C<sub>L</sub> = 50 pF. See [Figure 6](#)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			SN54HCT125 <sup>(1)</sup>		SN74HCT125		
					MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	Propagation delay	A	Y	4.5		11	20		39		25	ns
				5.5		10	18		35		22	
t <sub>en</sub>	Enable time	OE	Y	4.5		18	28		42		35	ns
				5.5		15	25		38		31	
t <sub>dis</sub>	Diable time	OE	Y	4.5		15	26		39		33	ns
				5.5		13	23		35		30	
t <sub>t</sub>	Transition time		Any	4.5		8	15		22		19	ns
				5.5		7	14		21		17	

(1) SN54HCT125 is in product preview.

## 5.5 Switching Characteristics

C<sub>L</sub> = 150 pF. See [Figure 6](#)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			SN54HCT125 <sup>(1)</sup>		SN74HCT125		
					MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	Propagation delay	A	Y	4.5		19	36		58		46	ns
				5.5		16	32		48		42	
t <sub>en</sub>	Enable time	OE	Y	4.5		25	40		60		50	ns
				5.5		21	35		53		43	
t <sub>t</sub>	Transition time		Any	4.5		17	42		63		53	ns
				5.5		14	38		57		48	

(1) SN54HCT125 is in product preview.

## 5.6 Operating Characteristics

$T_A = 25^\circ\text{C}$

		Test Conditions	TYP	UNIT
$C_{pd}$	Power dissipation capacitance	No load	35	pF

## 6 Parameter Measurement Information

$t_{pd}$  is the maximum between  $t_{PLH}$  and  $t_{PHL}$

$t_t$  is the maximum between  $t_{TLH}$  and  $t_{THL}$

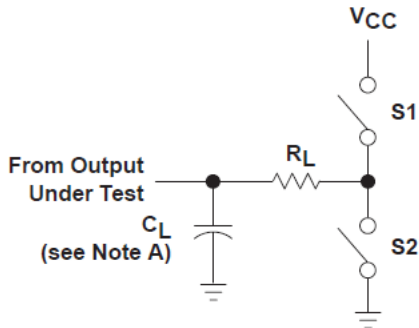


Figure 6-1. Load Circuit

PARAMETER		$R_L$	$C_L$	S1	S2
$t_{en}$	$t_{PZH}$	1 k $\Omega$	50 pF or 150 pF	Open	Closed
	$t_{PZL}$			Closed	Open
$t_{dis}$	$t_{PHZ}$	1 k $\Omega$	50 pF	Open	Closed
	$t_{PLZ}$			Closed	Open
$t_{pd}$ or $t_t$		—	50 pF or 150 pF	Open	Open

Figure 6-2.

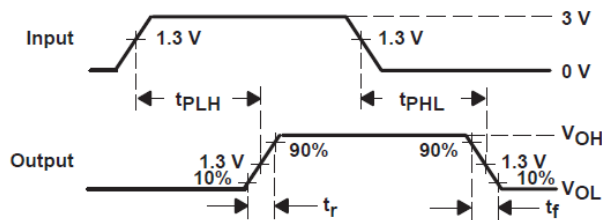


Figure 6-3. Voltage Waveforms Propagation Delay Times

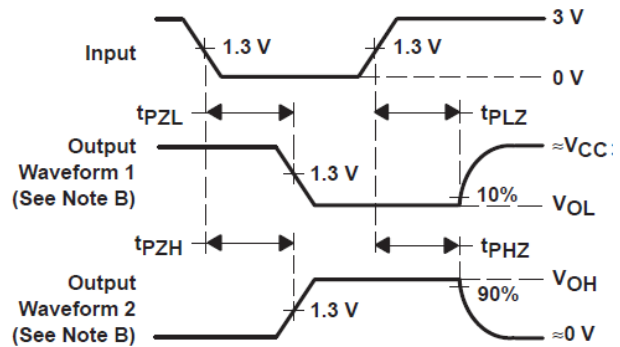


Figure 6-4. Voltage Waveforms Enable and Disable Times For 3-state Outputs

A.  $C_L$  includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.

Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1$  MHz,  $Z_O = 50 \Omega$ ,  $t_r = 6$  ns,  $t_f = 6$  ns.

D. The outputs are measured one at a time with one input transition per measurement.

E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .

F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .

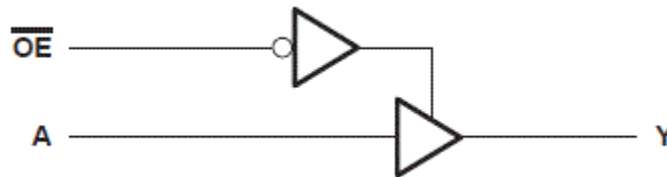
## 7 Detailed Description

### 7.1 Overview

These bus buffer gates feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable ( $\overline{OE}$ ) input is high.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

### 7.2 Functional Block Diagram



### 7.3 Device Functional Modes

**Table 7-1. Function Table  
(each gate)**

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z



## 8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu\text{F}$  capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu\text{F}$  and 1- $\mu\text{F}$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

## 9 Layout

### 9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

## 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 10.1 Documentation Support

#### 10.1.1 Related Documentation

### 10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 10.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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### 10.4 Trademarks

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### 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HCT125DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	HCT125	<a href="#">Samples</a>
SN74HCT125DRE4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT125	<a href="#">Samples</a>
SN74HCT125N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HCT125N	<a href="#">Samples</a>
SN74HCT125NE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HCT125N	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCT125DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCT125DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCT125DR	SOIC	D	14	2500	356.0	356.0	35.0
SN74HCT125DR	SOIC	D	14	2500	356.0	356.0	35.0

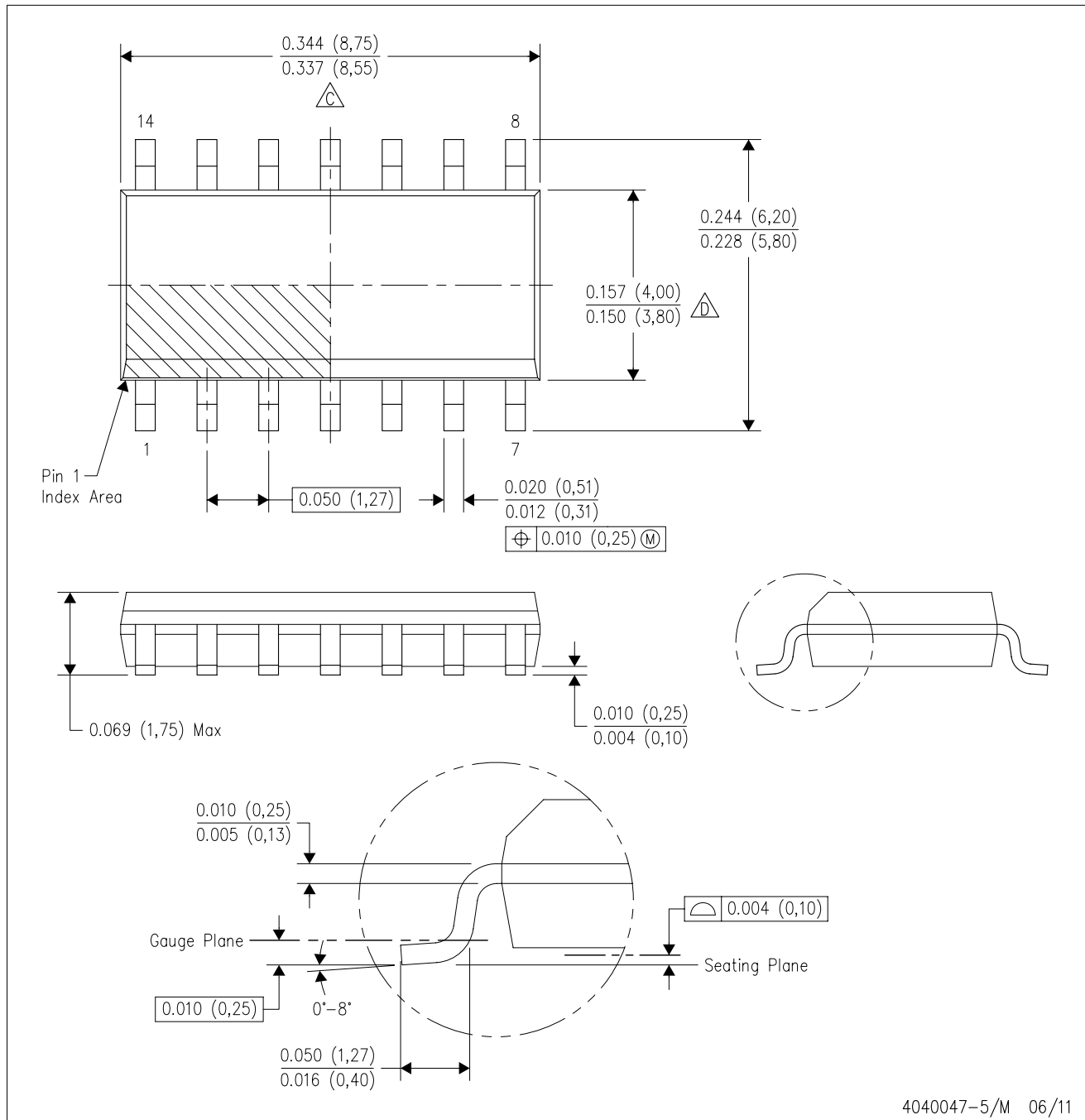
**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN74HCT125N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HCT125N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HCT125NE4	N	PDIP	14	25	506	13.97	11230	4.32
SN74HCT125NE4	N	PDIP	14	25	506	13.97	11230	4.32

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4040047-5/M 06/11

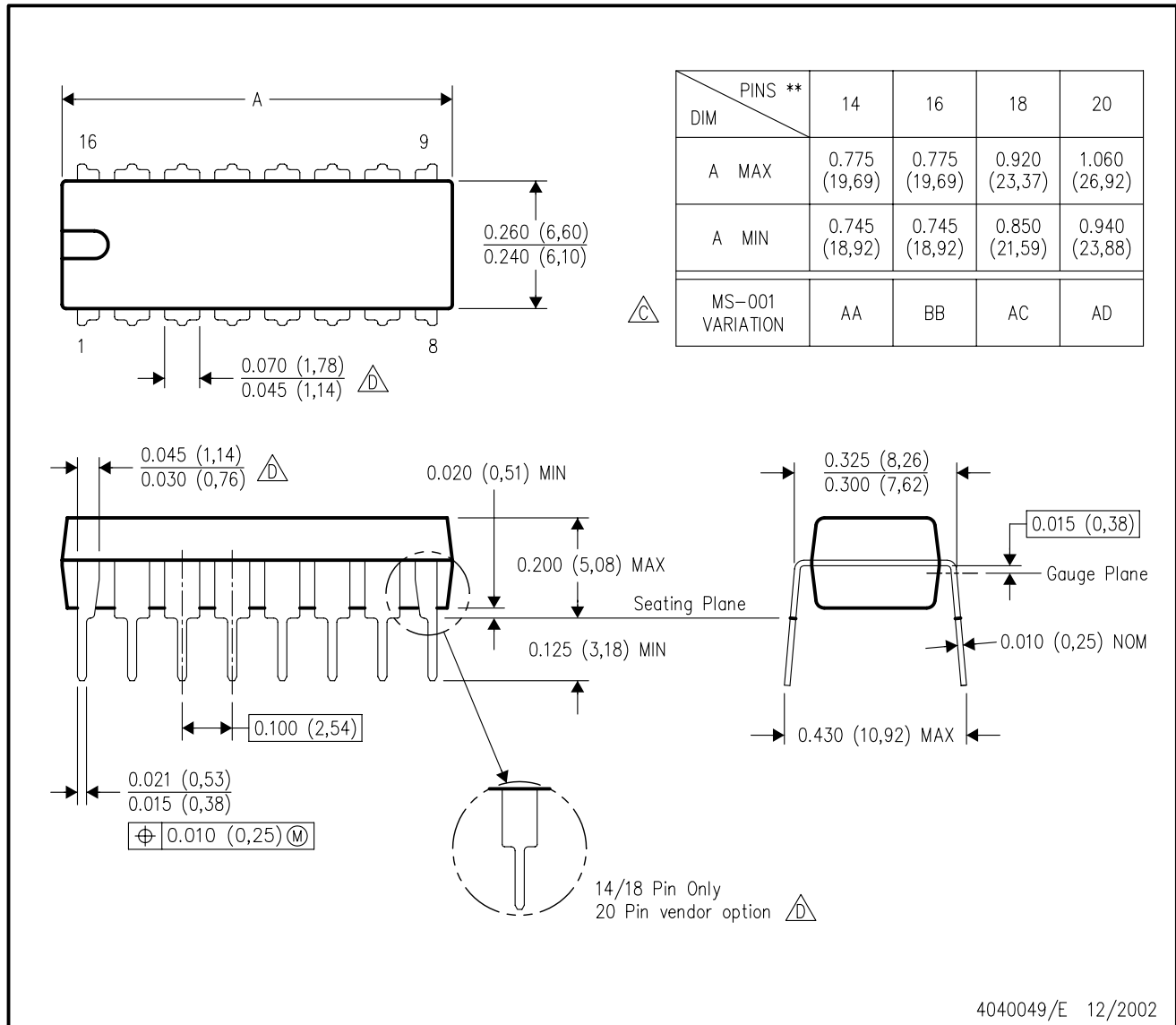
- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - $\triangle C$  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
  - $\triangle D$  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
  - E. Reference JEDEC MS-012 variation AB.



N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
  - The 20 pin end lead shoulder width is a vendor option, either half or full width.

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